



Vishay Siliconix

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0096			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0120			
I <sub>D</sub> (A)	32			
Configuration	Single			
Package	PowerPAK SO-8L			

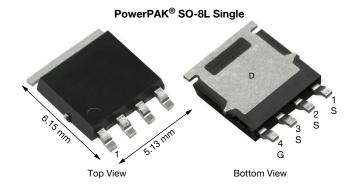
#### **FEATURES**

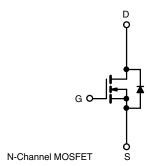
- TrenchFET® power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE





ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	60	V		
Gate-Source Voltage		$V_{GS}$	± 20	v		
Continuous Drain Current a	T <sub>C</sub> = 25 °C	1	32			
Continuous Drain Current "	T <sub>C</sub> = 125 °C	I <sub>D</sub>	32			
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	32	Α			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	128				
Single Pulse Avalanche Current		I <sub>AS</sub>	38			
Single Pulse Avalanche Energy	L = 0.1 mH		72	mJ		
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	83	W		
waximum Fower Dissipation -	T <sub>C</sub> = 125 °C	$P_{D}$	27			
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C			
Operating Junction and Storage Temperature Range  Soldering Recommendations (Peak Temperature) d, e			260			

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	nction-to-Ambient PCB Mount <sup>c</sup>		65	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.8	C/VV	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static	,				<u> </u>		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		2.0	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1	μА
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	1	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 18 A	1	0.0083	0.0096	
Drain-Source On-State Resistance a	В	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 18 A, T <sub>J</sub> = 125 °C	-	-	0.0162	Ω
Drain-Source On-State Resistance 4	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 18 A, T <sub>J</sub> = 175 °C	-	-	0.0200	12
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 15 A	=	0.0101	0.0120	]
Forward Transconductance b	9fs	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		-	60	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	ı	3836	4795	pF
Output Capacitance	Coss	$V_{GS} = 0 V$		1	393	495	
Reverse Transfer Capacitance	C <sub>rss</sub>			1	188	235	
Total Gate Charge <sup>c</sup>	$Q_{g}$		V <sub>DS</sub> = 30 V, I <sub>D</sub> = 18 A	ı	71	106	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = 10 V		1	9.7	-	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			1	12.5	-	
Gate Resistance	$R_g$	f = 1 MHz		0.5	-	3.2	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>				12	18	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 30 \text{ V}, \text{ R}_L = 30 \Omega$ $I_D \cong 1 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		1	11	17	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	56	84	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	25	32	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			1	-	128	Α
Forward Voltage	$V_{SD}$	l <sub>F</sub> :	-	0.8	1.2	V	

#### Notes

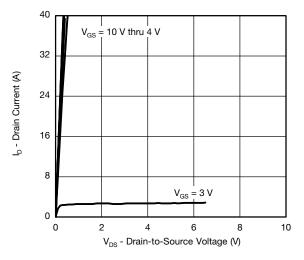
- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

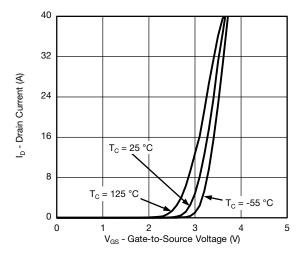
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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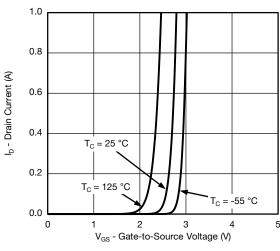
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

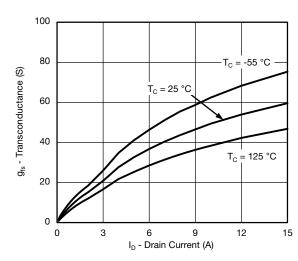




#### **Output Characteristics**

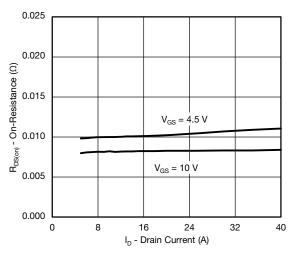


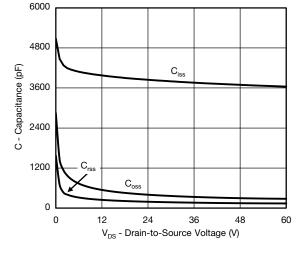




### Transfer Characteristics

Transconductance



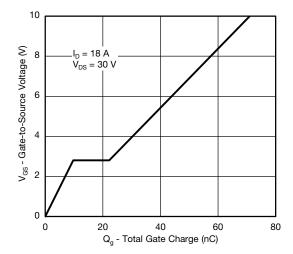


On-Resistance vs. Drain Current

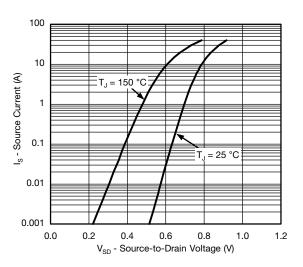


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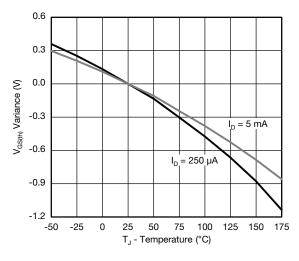
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



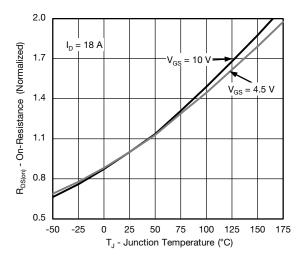
**Gate Charge** 



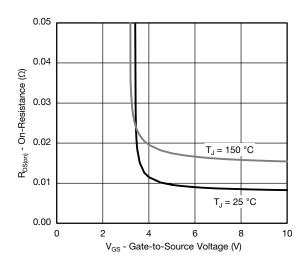
**Source Drain Diode Forward Voltage** 



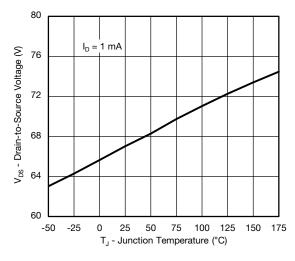
**Threshold Voltage** 



On-Resistance vs. Junction Temperature



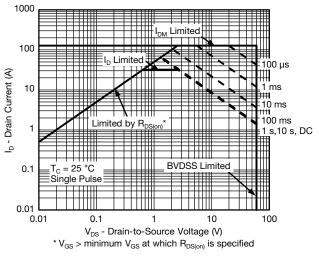
On-Resistance vs. Gate-to-Source Voltage



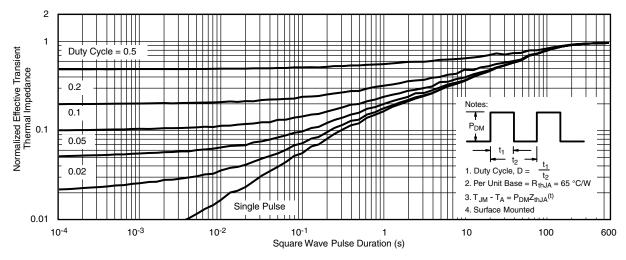
Drain Source Breakdown vs. Junction Temperature

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## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Safe Operating Area

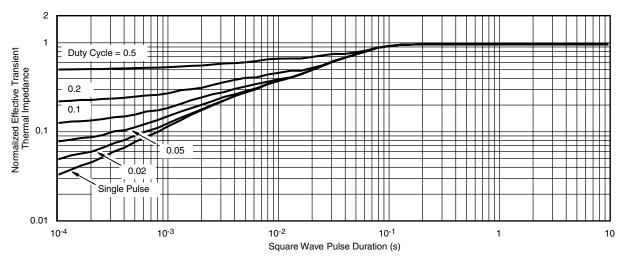


Normalized Thermal Transient Impedance, Junction-to-Ambient



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#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67034.

### Work-In-Progress



www.vishay.com

# SQJ460EP

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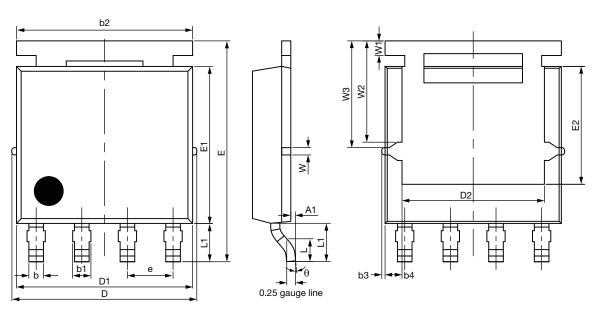
REVISION	HISTORY a	
REVISION	DATE	DESCRIPTION OF CHANGE
В	04-Aug-15	Revised R <sub>g</sub> minimum limit

### Note

a. As of April 2014

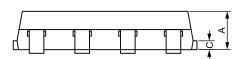


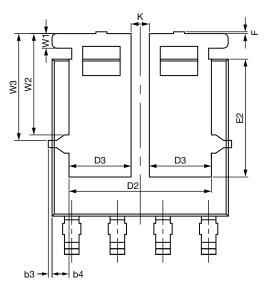
# PowerPAK® SO-8L Case Outline 1



Topside view

Backside view (single)





Backside view (dual)



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DIM	MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3		0.094	•		0.004	
b4		0.47			0.019	
С	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
е		1.27 BSC		0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K		0.51			0.020	
W	0.23			0.009		
W1	0.41			0.016		
W2	2.82			0.111		
W3		2.96		0.117		
θ	0°	-	10°	0°	-	10°

ECN: S19-0643-Rev. E, 05-Aug-2019

DWG: 5976

#### Note

• Millimeters will gover



#### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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